

SEMICONDUCTOR WAFER AND PROCESSING METHOD FOR SAME

Abstract of the Disclosure

A semiconductor wafer which is generally circular,
and which has on its face an annular surplus region
5 present in an outer peripheral edge portion of the face,
and a circular device region surrounded by the surplus
region, the device region having many semiconductor
devices disposed therein. A circular concavity is formed
in the back of the semiconductor wafer in correspondence
10 with the device region, and the device region is
relatively thin, while the surplus region is relatively
thick.

Figure 3